



2CBF01,2CBF03,2CBF05

GLASS PASSIVATED SILICON ULTRAFAST RECOVERY DIODE

Features:

1. Silicon diffusion mesa.
2. Glass Passivated package.
3. Small volume, light weight.
4. Small high-temperature leakage.
5. Good thermal stability.
6. High reliability.
7. Implementation of standards: GJB33A-97, QZJ840611A, QZJ840611



TECHNICAL DATA:

($T_a = 25^\circ\text{C}$)

Parameter name	Symbols	Unit	Specifications			Test Condition
			2CBF01	2CBF03	2CBF05	
Use for	Ultra-high-frequency rectifier,switch circuit.					
Store temperature	T	$^\circ\text{C}$	-55~+150			
Quality Class			JP, JT, JCT, GS, G, G+			
Peak Repetitive Reverse Voltage	V_{RRM}	V	2000~8000			
Average Forward Current	$I_{F(AV)}$	A	0.1	0.3	0.5	
Average Forward Voltage	V_F	V	B~E:8, F~H:10			$I=I_{F(AV)}$
Non-repeat Forward Surge Current	I_{FSM}	A	2	6	8	Single-phase industrial frequency sine half wave 10ms
Peak Reverse Current	I_{RM1}	μA	10			$V_R=V_{RRM}, T_a=25^\circ\text{C}$
Peak Reverse Current	I_{RM2}	μA	200			$V_R=V_{RRM}, T_a=125^\circ\text{C}$
Junction Temperature	T_{jm}	$^\circ\text{C}$	125			
Reverse Recovery Time	t_{rr}	μS	0.2			$V_R=10\text{V}, I_F=50\text{mA}, R_L=75\text{ohms}$

SPECIFICATIONS:

B	C	D	E	F	G	H
2000V	3000V	4000V	5000V	6000V	7000V	8000V

Outline and Dimensions: